

# PESC10120Y-R

Silicon Carbide 1200V Schottky Diode

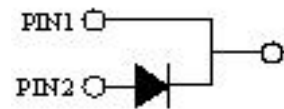
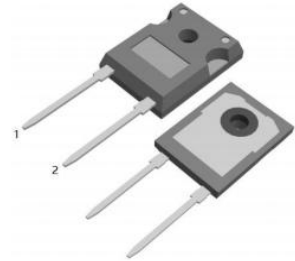


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## Features

- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- Optimized for high temperature operation
- Qualified according to JEDEC criteria

TO-247-2L



## Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply

## Description

- System efficiency improvement over Si diodes
- Enabling higher frequency / increased power density solutions
- System size/cost savings due to reduced heatsink requirements and smaller magnetics
- Reduced EMI
- Highest efficiency across the entire load range
- Robust diode operation during surge events
- High reliability



## Key performance parameters

### Product Summary

$V_{DC}$	1200V
$I_F$	10A
$T_{j,max}$	175°C

### Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PESC10120Y-R	PESC10120Y	TO-247-2L	Tube	N/A	N/A	30pcs

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## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	1200	V
Continuous forward current for $T_C = 150^\circ\text{C}$	$I_F$	10	A
Non-Repetitive Peak Forward Surge Current $T_C=25^\circ\text{C}, t_p=8.3\text{ ms}$ , Half Sine Pulse $T_C=150^\circ\text{C}, t_p=8.3\text{ ms}$ , Half Sine Pulse	$I_{FSM}$	100 75	A
$i^2t$ value $T_C = 25^\circ\text{C}$ , $t_p=8.3\text{ ms}$ $i^2t$ value $T_C = 150^\circ\text{C}$ , $t_p=8.3\text{ ms}$	$\int i^2dt$	42 23	$\text{A}^2\text{s}$
Total power dissipation $T_C = 25^\circ\text{C}$	$P_D$	114	W
Operating junction and storage temperature	$T_j, T_{stg}$	-55 to +175	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	$T_{sold}$	260	$^\circ\text{C}$

### Thermal Resistance

Parameter	Symbol	Condition	Value			Unit
			min.	typ.	max.	
Thermal resistance, junction - case.	$R_{thJC}$		-	0.9	1.3	°C/W
Thermal resistance, junction - ambient(min. footprint)	$R_{thJA}$		-		50	°C/W

### Electrical Characteristic

#### Static Characteristic ( $T_j=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
DC blocking voltage	$V_{DC}$	$I_R=100\mu\text{A}$	1200	-	-	V
Forward voltage	$V_F$	$I_F=10\text{A}, T_j=25^\circ\text{C}$	-	1.5	1.8	V
		$I_F=10\text{A}, T_j=150^\circ\text{C}$	-	2.0	2.4	V
Reverse current	$I_R$	$V_R=1200\text{V}, T_j=25^\circ\text{C}$		1	10	$\mu\text{A}$
		$V_R=1200\text{V}, T_j=150^\circ\text{C}$	-	10	100	

#### Dynamic Characteristic ( $T_j=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
Total capacitance	C	$V_R=0.1\text{V}, f=1\text{MHz}$	-	653	-	pF
		$V_R=400\text{V}, f=1\text{MHz}$	-	44	-	
		$V_R=800\text{V}, f=1\text{MHz}$	-	35	-	
Total capacitive charge	$Q_C$	$V_R=800\text{V}, Q_C = \int_0^{V_R} C(V)dV$	-	47	-	nC

### Typical Performance Characteristics

Fig 1: Forward Characteristics

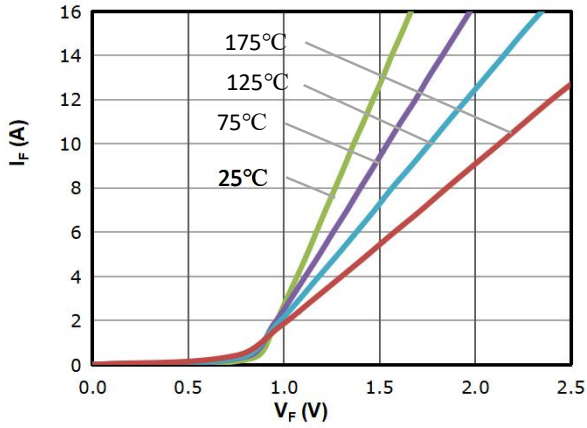


Fig 2: Reverse Characteristics

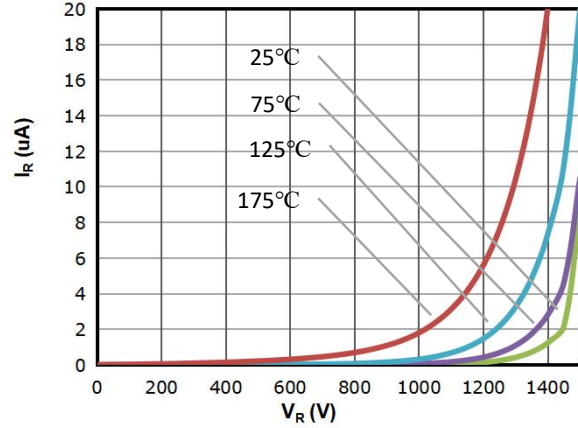


Fig 3: Total Capacitance Charge VS. Reverse Voltage

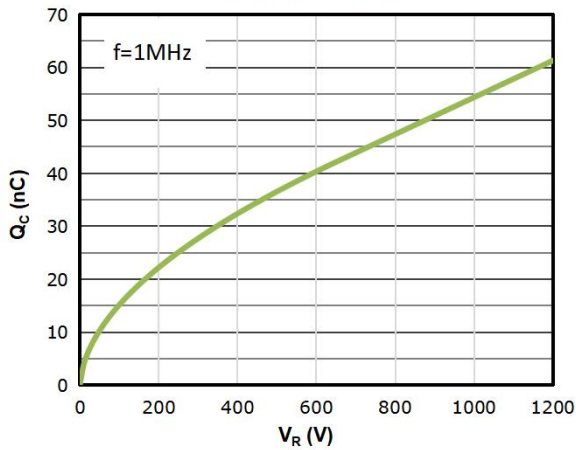


Fig 4: Capacitance Characteristics

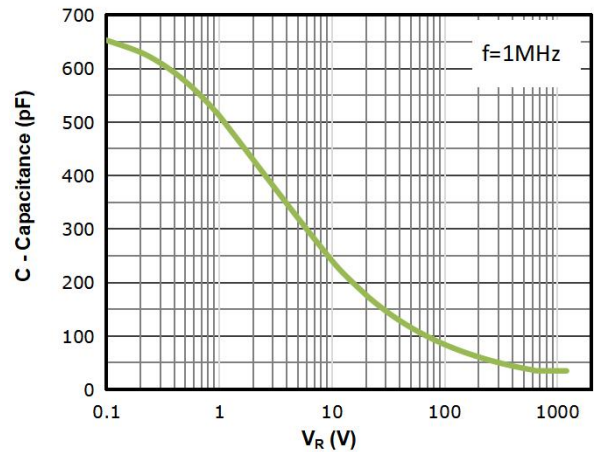


Fig 5: Power Dissipation

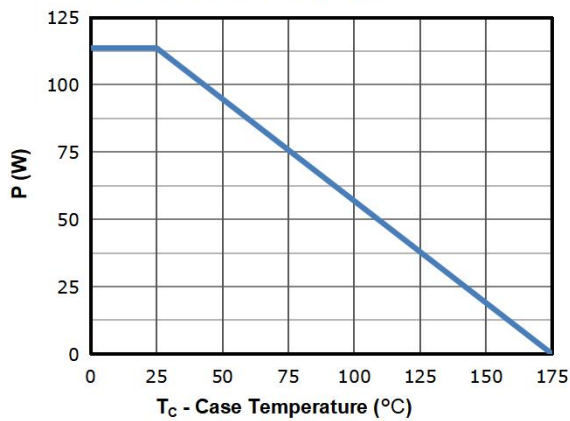
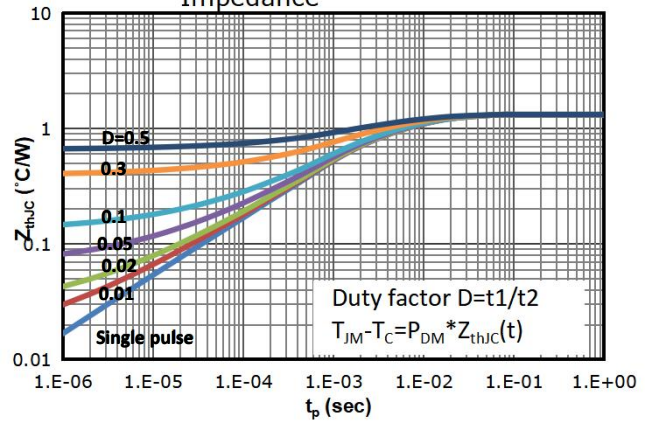
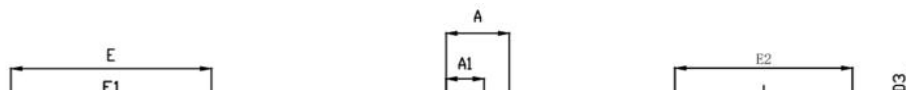


Fig 6: Max. Transient Thermal Impedance



### Package Outline: TO-247-2L

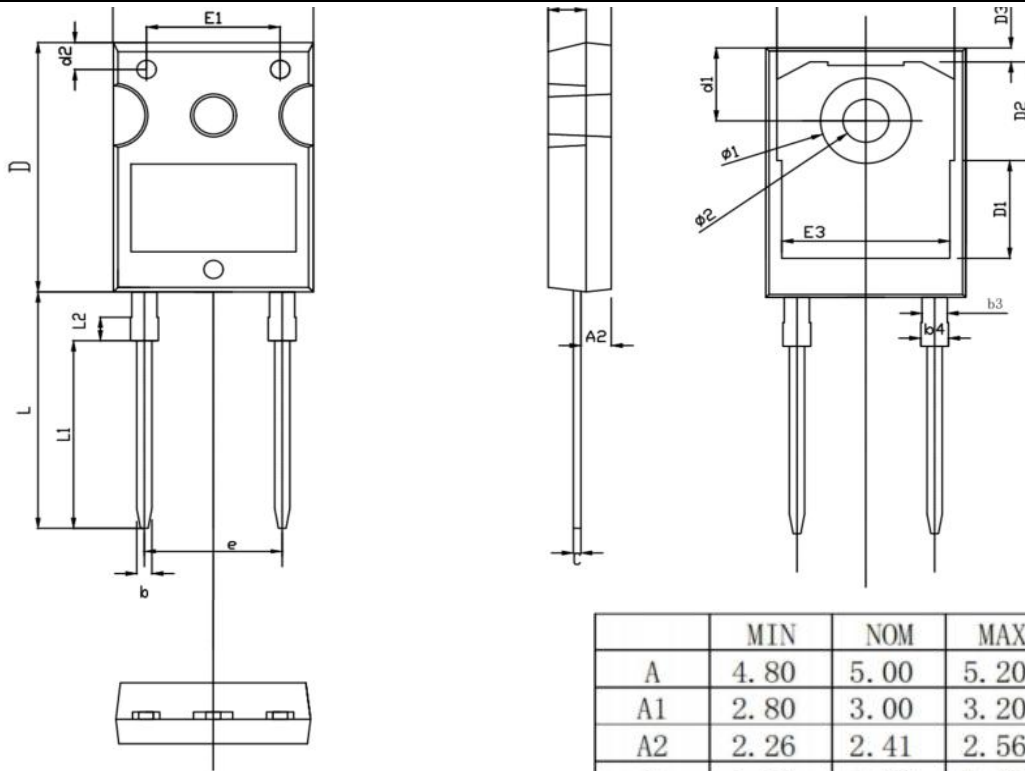


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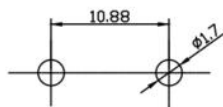
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RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.80	3.00	3.20
A2	2.26	2.41	2.56
b	1.10	1.20	1.30
b3	1.90	2.00	2.10
b4	2.00	-	2.20
c	0.50	0.60	0.70
D	20.80	21.00	21.20
D1	8.03	8.23	8.43
D2	8.12	8.32	8.52
D3	0.97	1.17	1.37
d1	6.00	6.15	6.30
d2	2.20	2.30	2.40
E	15.60	15.80	16.00
E1	10.30	10.50	10.70
E2	13.82	14.02	14.22
E3	13.30	13.50	13.70
e	10.68	10.88	11.08
L	19.72	19.92	20.12
L1	15.59	15.79	15.99
L2	1.78	1.98	2.18
Ø1	7.10	7.19	7.30
Ø2	3.50	3.60	3.70



### Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

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